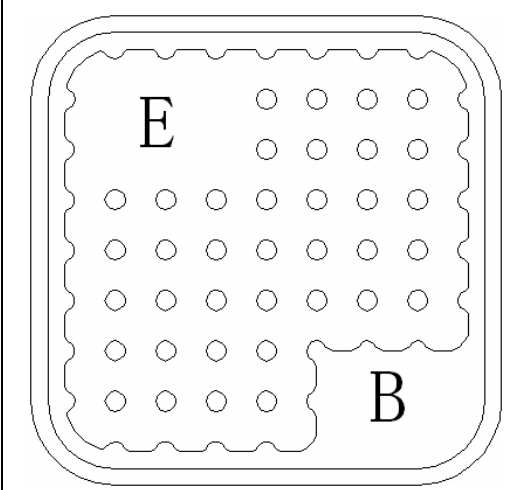


D880A Silicon NPN Epitaxial Transistor

Description: The D880A is designed for audio frequency general amplifier applications and power pumping!

Features: ●Excellent h_{FE} Linearity
●Complementary to B834A

Chip Appearance

	Chip Size		1500um×1500um
	Chip Thickness		210±20um
	Bonding Pad Size	Base	465um×315um
		Emitter	425um×300um
	Front Metal		Al
	Backside Metal		TiNiAg/Au (As)
	Scribe line width		70um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=50\text{ V}$, $I_E=0$		0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5\text{ V}$, $I_C=0$		0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu\text{A}$, $I_E=0$	60		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1\text{ mA}$, $I_B=0$	60		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu\text{A}$, $I_C=0$	7		V
DC Current Gain	h_{FE}	$V_{CE}=5\text{ V}$, $I_C=0.5\text{ A}$	100	300	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=3\text{ A}$, $I_B=0.3\text{ A}$		1	V